

Apparatus and Method of Manufacture for Integrated Circuit and CMOS Device Including Epitaxially Grown Dielectric on Silicon Carbide

Abstract of the Disclosure

5 An integrated circuit, or portion thereof, such as a CMOS device, includes an epitaxially grown dielectric on a silicon carbide base. The epitaxially grown dielectric forms a gate dielectric and the silicon carbide base serves as a channel region for the CMOS device. In various embodiments, the epitaxially grown dielectric may be a crystalline carbon or carbon-containing film.